

FC809

Silicon Barrier Diode

30V, 70mA Rectifier

Applications

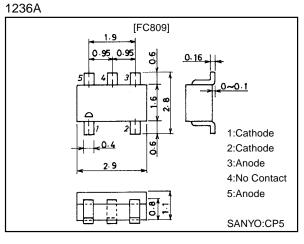
- · General rectification applications.
- High frequency rectification (switching regulators, converters, choppers).

Features

- · Low forward voltage (V_F max=0.55V).
- \cdot Fast reverse recovery time (trr max=10ns).
- Composite type with 2 diodes contained in the CP package currently in use, saving the mounting space greatly.
- The FC809 is formed with two chips, each being equivalent to the SB007-03CP, placed in one package.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C (Value per element)

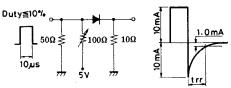
Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	VRRM		30	V
Nonrepetitive Peak Reverse Surge Voltage	V _{RSM}		35	V
Average Output Current	lo		70	mA
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	2	A
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

Electrical Characteristics at Ta = 25°C (Value per element)

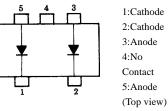
.Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	
Reverse Voltage	VR	I _R =20μΑ	30			V
Forward Voltage	VF	I _F =70mA			0.55	V
Reverse Current	I _R	V _R =15V			5.0	μA
Interteminal Capacitance	С	V _R =10V, f=1MHz		3.0		pF
Reverse Recovery Time	trr	IF=IR=10mA, See specified Test Circuit			10	ns
Thermal Resistance	Rth (j-a)			560		°C/W

· Marking:809

trr Test Circuit

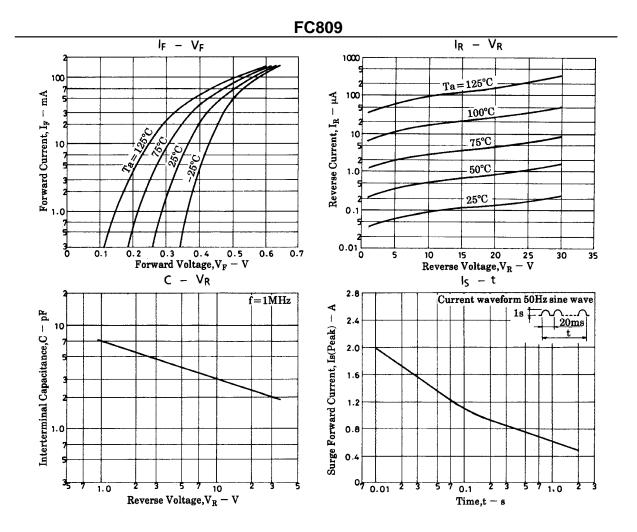


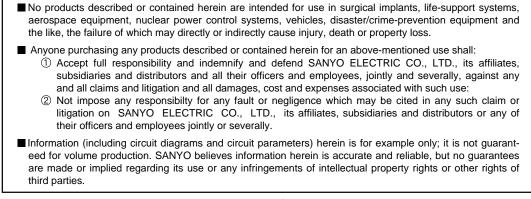
Electrical Connection



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